FAIRCHILD SEMICONDUCTOR®

October 2013

FQB22P10

P-Channel QFET® MOSFET

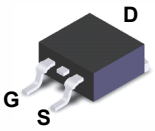
-100 V, -22 A, 125 mΩ

Description

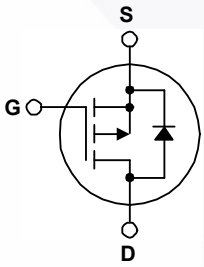
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -22 A, -100 V, $R_{DS(on)}$ = 125 mΩ (Max) @V_{GS} = -10 V, I_D = -11 A
- Low Gate Charge (Typ. 40 nC)
- Low Crss (Typ. 160 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



D^2-PAK



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQB22P10TM	Unit
V_{DSS}	Drain-Source Voltage		-100	V
I_D	Drain Current - Continuous (T_C = 25°C)		-22	A
	Drain Current - Continuous (T_C = 100°C)		-15.6	A
I_{DM}	Drain Current - Pulsed	(Note 1)	-88	A
V_{GSS}	Gate-Source Voltage		±30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	710	mJ
I_{AR}	Avalanche Current	(Note 1)	-22	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	12.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns
P_D	Power Dissipation (T_A = 25°C) *		3.75	W
	Power Dissipation (T_C = 25°C)		125	W
	- Derate above 25°C		0.83	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB22P10TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (* 1 in^2 pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB22P10	FQB22P10TM	D2-PAK	330mm	24mm	800

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-100	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = -250 µA, Referenced to 25°C	--	-0.1	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -100 V, V_{GS} = 0 V	--	--	-1	µA
		V_{DS} = -80 V, T_C = 125°C	--	--	-10	µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = -10 V, I_D = -11 A	--	0.096	0.125	Ω
g_{FS}	Forward Transconductance	V_{DS} = -40 V, I_D = -11 A	--	13.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1170	1500	pF
C_{oss}	Output Capacitance		--	460	600	pF
C_{rss}	Reverse Transfer Capacitance		--	160	200	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -50 V, I_D = -22 A, R_G = 25 Ω (Note 4)	--	17	45	ns
t_r	Turn-On Rise Time		--	170	350	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Turn-Off Fall Time		--	110	230	ns
Q_g	Total Gate Charge	V_{DS} = -80 V, I_D = -22 A, V_{GS} = -10 V (Note 4)	--	40	50	nC
Q_{gs}	Gate-Source Charge		--	7.0	--	nC
Q_{gd}	Gate-Drain Charge		--	21	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-22	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-88	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -22 A	--	--	-4.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = -22 A, dI_F / dt = 100 A/µs	--	110	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.6	--	µC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 2.2mH, I_{AS} = -22A, V_{DD} = -25V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ -22A, di/dt ≤ 300A/µs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially independent of operating temperature

Typical Characteristics

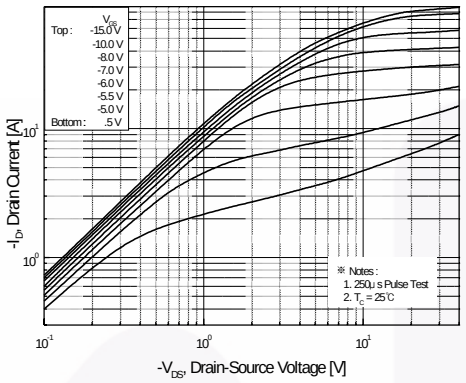


Figure 1. On-Region Characteristics

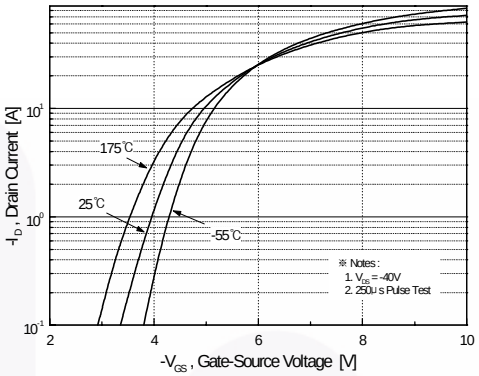


Figure 2. Transfer Characteristics

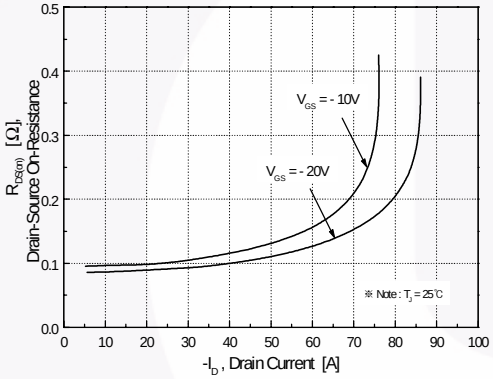


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

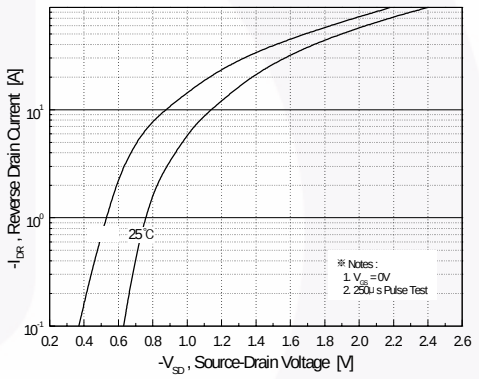


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

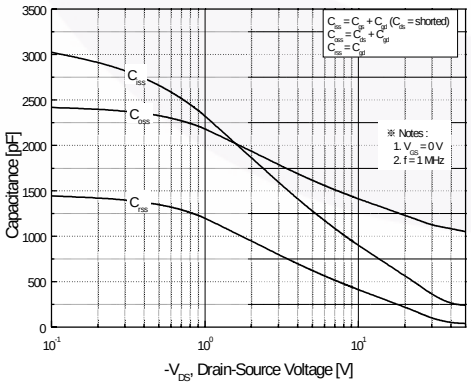


Figure 5. Capacitance Characteristics

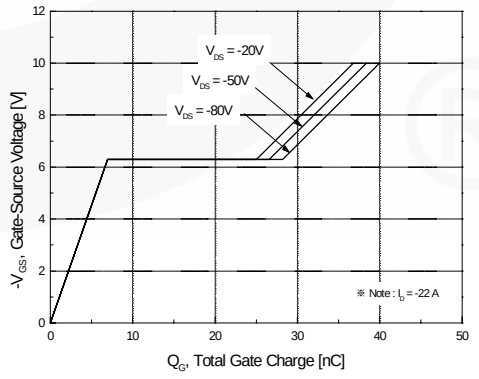


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

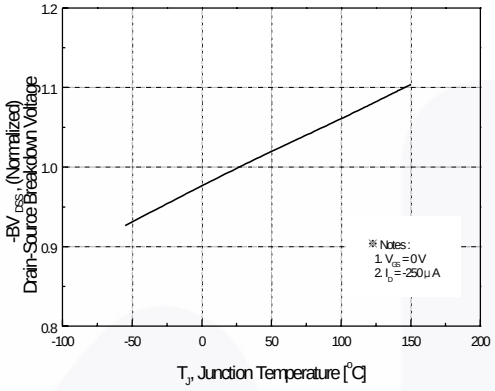


Figure 7. Breakdown Voltage Variation vs. Temperature

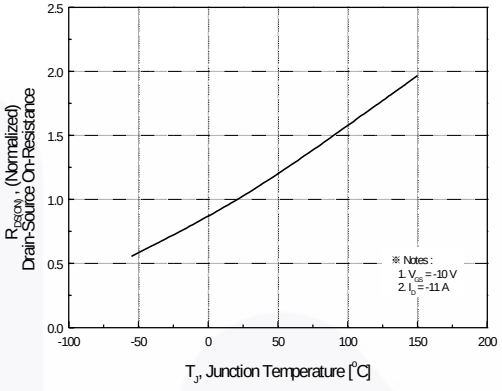


Figure 8. On-Resistance Variation vs. Temperature

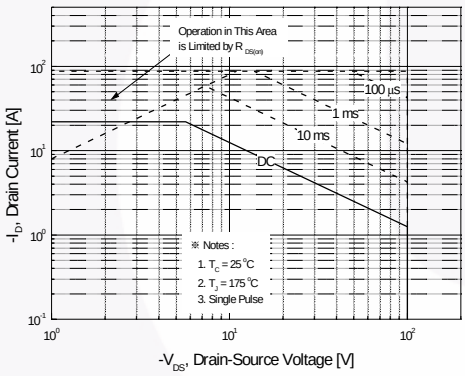


Figure 9. Maximum Safe Operating Area

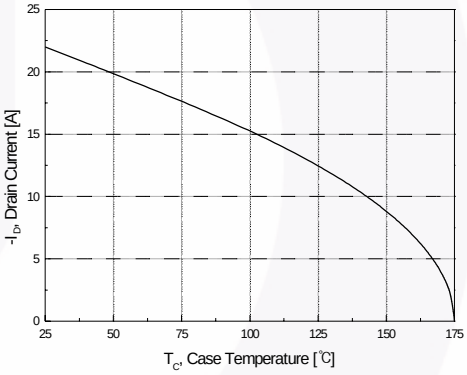


Figure 10. Maximum Drain Current vs. Case Temperature

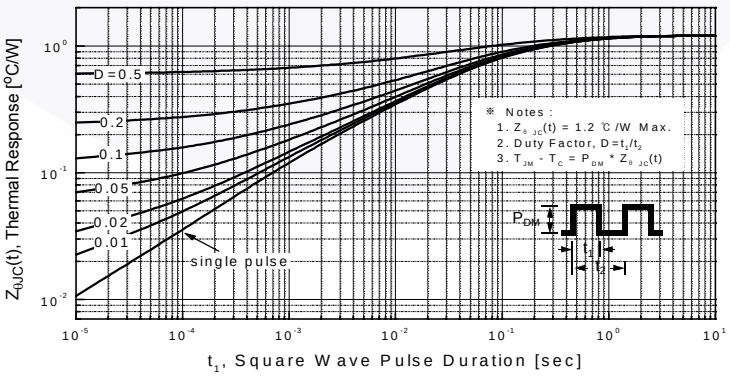


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

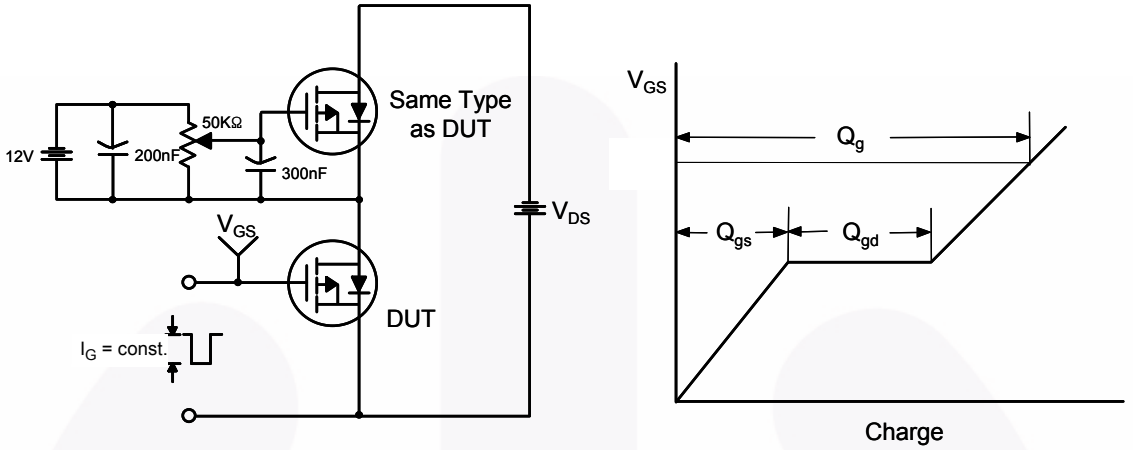


Figure 13. Resistive Switching Test Circuit & Waveforms

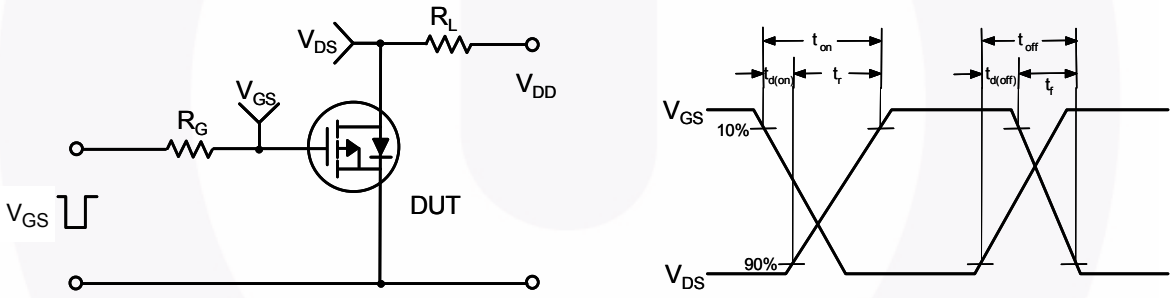


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

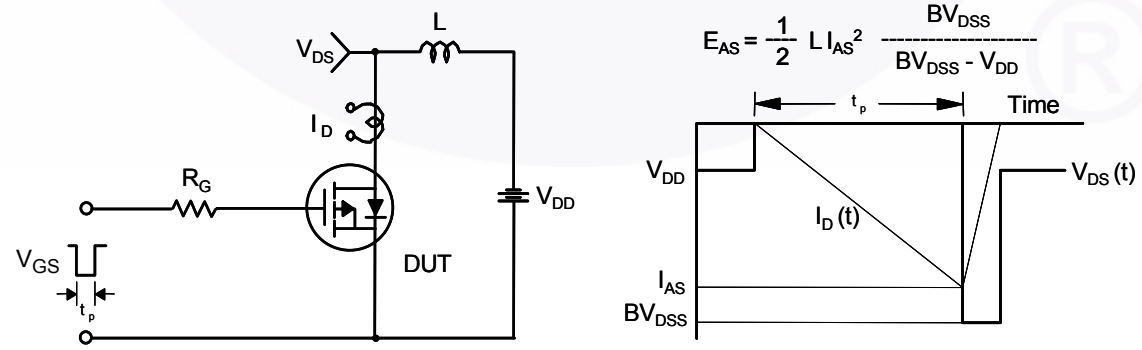
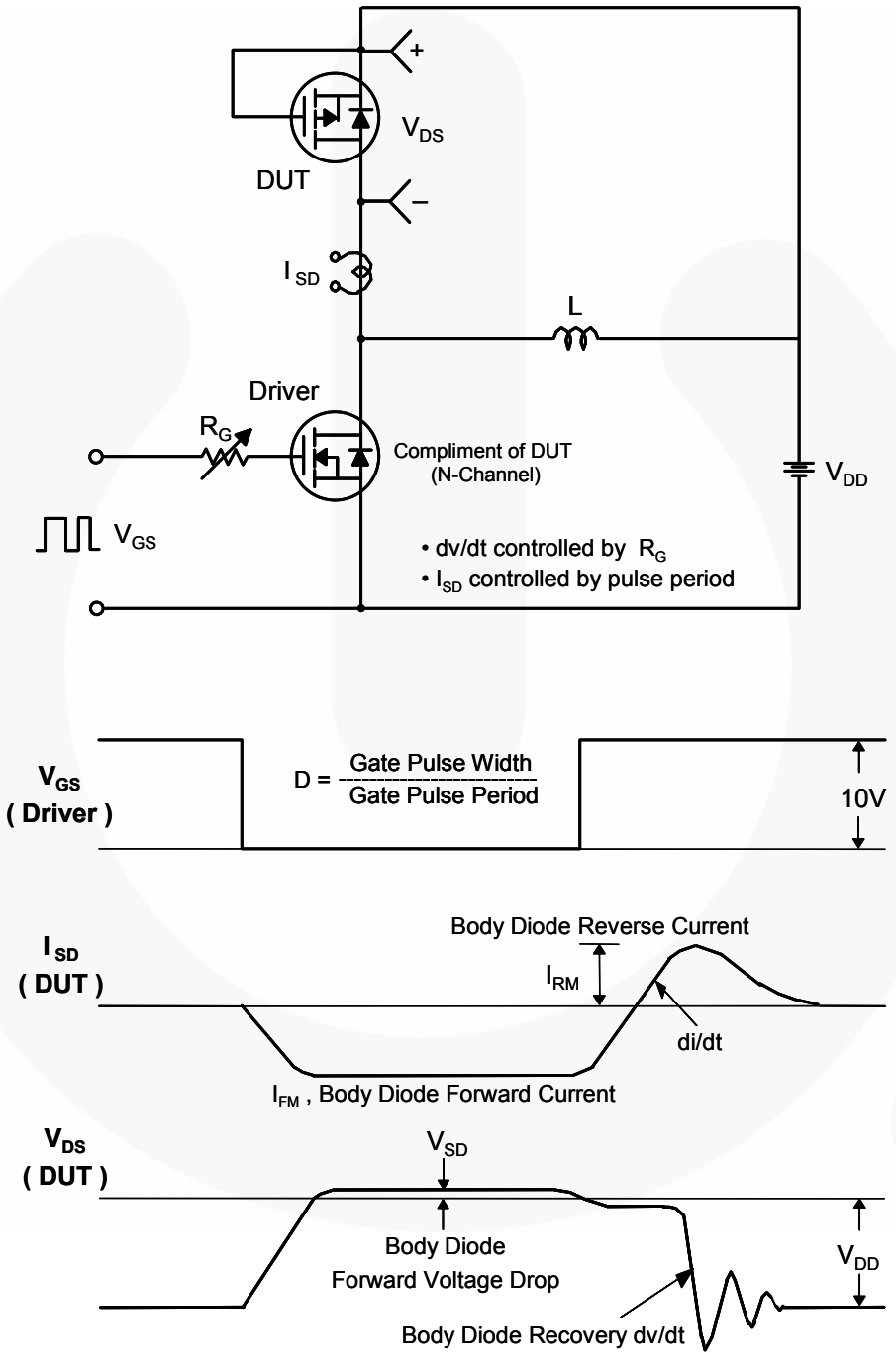
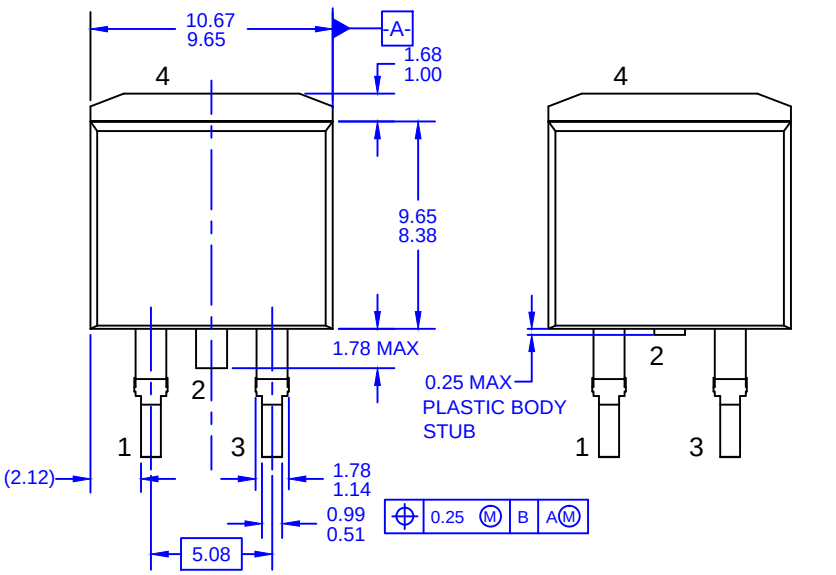
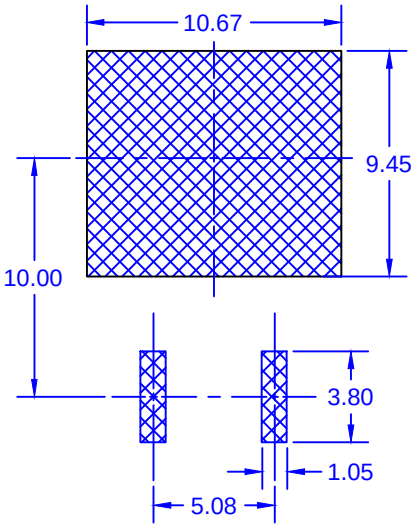


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

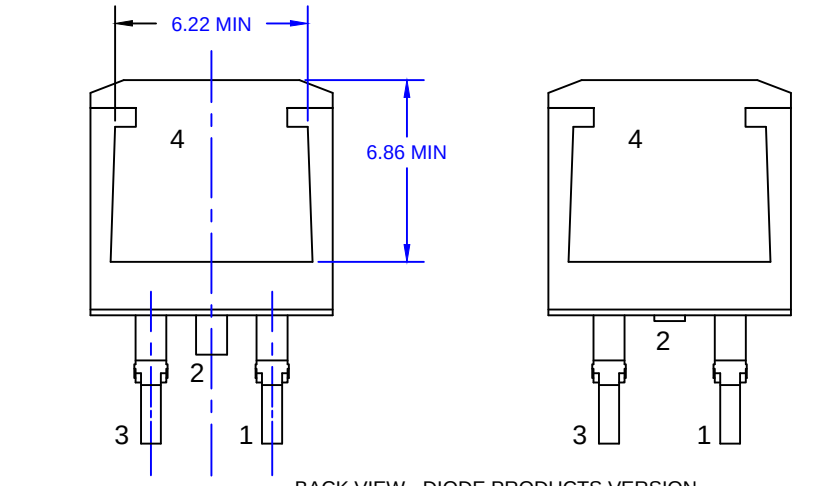




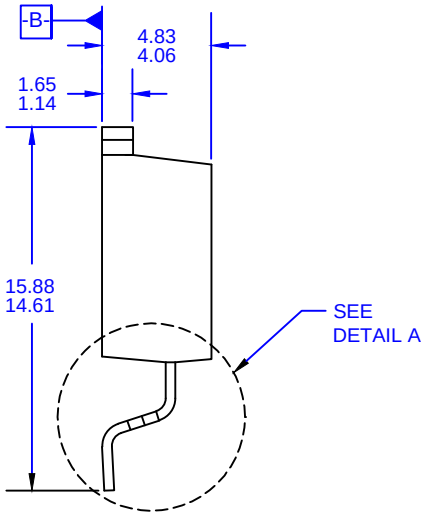
FRONT VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL

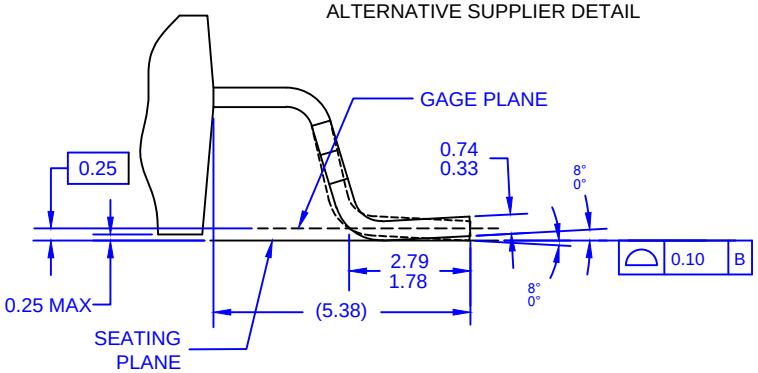


BACK VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) REFERENCE JEDEC, TO-263, VARIATION AB.
C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
F) FILENAME: TO263A02REV8



DETAIL A, ROTATED 90°
SCALE: 2X

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